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Shunt Regulator



ADE-204-049A (Z)

Rev.1 Sep. 2002

### Description

The HA17431 series is temperature-compensated variable shunt regulators. The main application of these products is in voltage regulators that provide a variable output voltage. The on-chip high-precision reference voltage source can provide  $\pm 1\%$  accuracy in the V versions, which have a V<sub>KA</sub> max of 16 volts. The HA17431VLP, which is provided in the MPAK-5 package, is designed for use in switching mode power supplies. It provides a built-in photocoupler bypass resistor for the PS pin, and an error amplifier can be easily constructed on the supply side.

#### Features

- The V versions provide 2.500 V  $\pm 1\%$  at Ta = 25°C
- The HA17431VLP includes a photocoupler bypass resistor (2 k $\Omega$ )
- The reference voltage has a low temperature coefficient
- The MPAK-5(5-pin), MPAK(3-pin) and UPAK miniature packages are optimal for use on high mounting density circuit boards
- Car use is provided

### **Block Diagram**



### **Application Circuit Example**



### **Ordering Information**

		Version				Operating	
Item		V Version	A Version	Normal Version	Package	Temperature Range	
Reference	Accuracy	±1%	±2.2%	±4%			
voltage (at 25°C)	Max	2.525 V	2.550 V	2.595 V			
	Тур	2.500 V	2.495 V	2.495 V			
	Min	2.475 V	2.440 V	2.395 V			
Cathode voltage		16 V max	40 V max	40 V max			
Cathode curr	rent	50 mA max	150 mA max	150 mA max			
Car use		HA17431VPJ			TO-92	–40 to +85°C	
			HA17431PNAJ				
			HA17431PAJ		TO-92MOD	-	
				HA17431PJ			
			HA17431FPAJ		FP-8D	-	
			_	HA17431FPJ			

### **Ordering Information** (cont.)

	Version				Operating
Item	V Version	A Version	Normal Version	Package	Temperature Range
Industrial use	HA17431VLTP			MPAK	–20 to +85°C
	HA17432VLTP		_		
	HA17431VLP			MPAK-5	-
	HA17431VP			TO-92	-
		HA17431PNA		_	
	HA17431VUP			UPAK	-
		HA17431UPA		_	
	HA17432VUP			_	
		HA17432UPA		_	
		HA17431PA		TO-92MOD	-
			HA17431P		_
		HA17431FPA		FP-8D	
			HA17431FP		_
Commercial use		HA17431UA		UPAK	
		HA17432UA			

### **Pin Arrangement**



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### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	HA17431VLP	HA17431VP	HA17431VPJ	Unit	Notes
Cathode voltage	V <sub>ka</sub>	16	16	16	V	1
PS term. voltage	$V_{_{PS}}$	$V_{\rm KA}$ to 16	_	_	V	1,2,3
Continuous cathode current	Ι <sub>κ</sub>	-50 to +50	–50 to +50	–50 to +50	mA	
Reference input current	Iref	-0.05 to +10	-0.05 to +10	–0.05 to +10	mA	
Power dissipation	Ρ <sub>τ</sub>	150 *4	500 * <sup>5</sup>	500 * <sup>5</sup>	mW	4, 5
Operating temperature range	Topr	-20 to +85	-20 to +85	-40 to +85	°C	
Storage temperature	Tstg	-55 to +150	–55 to +150	–55 to +150		°C

Item	Symbol	HA17431VUP/HA17432VUP	HA17431VLTP/HA17432VLTP	Unit	Notes
Cathode voltage	V <sub>ka</sub>	16	16	V	1
PS term. voltage	$V_{_{PS}}$	_	—	V	1,2,3
Continuous cathode current	Ι <sub>κ</sub>	–50 to +50	–50 to +50	mA	
Reference input current	Iref	–0.05 to +10	–0.05 to +10	mA	
Power dissipation	Ρ <sub>τ</sub>	800 *8	150 *4	mW	4, 8
Operating temperature range	Topr	-20 to +85	20 to +85	°C	
Storage temperature	Tstg	–55 to +150	–55 to +150	°C	

Item	Symbol	HA17431PNA	HA17431P/PA	HA17431FP/FPA	HA17431UA/UPA/ HA17432UA/UPA	Unit	Notes
Cathode voltage	$V_{\kappa a}$	40	40	40	40	V	1
Continuous cathode current	Ι <sub>κ</sub>	-100 to +150	-100 to +150	-100 to +150	-100 to +150	mA	
Reference input current	Iref	-0.05 to +10	-0.05 to +10	-0.05 to +10	-0.05 to +10	mA	
Power dissipation	Ρ <sub>τ</sub>	500 * <sup>5</sup>	800 *6	500 * <sup>7</sup>	800 *8	mW	5,6,7,8
Operating temperature range	Topr	–20 to +85	-20 to +85	–20 to +85	-20 to +85	°C	
Storage temperature	Tstg	–55 to +150	-55 to +150	-55 to +125	-55 to +150	°C	



#### Absolute Maximum Ratings (cont.)

#### $(Ta = 25^{\circ}C)$

Item	Symbol	HA17431PNAJ	HA17431PJ/PAJ	HA17431FPJ/FPAJ	Unit	Notes
Cathode voltage	$V_{\rm ka}$	40	40	40	V	1
Continuous cathode current	Ι <sub>κ</sub>	-100 to +150	-100 to +150	-100 to +150	mA	
Reference input current	Iref	–0.05 to +10	-0.05 to +10	–0.05 to +10	mA	
Power dissipation	Ρ <sub>τ</sub>	500 *5	800 *6	500 *7	mW	5,6,7
Operating temperature range	Topr	–40 to +85	–40 to +85	–40 to +85	°C	
Storage temperature	Tstg	-55 to +150	-55 to +150	-55 to +125	°C	

Notes: 1. Voltages are referenced to anode.

- 2. The PS pin is only provided by the HA17431VLP.
- 3. The PS pin voltage must not fall below the cathode voltage. If the PS pin is not used, the PS pin is recommended to be connected with the cathode.
- 4. Ta  $\leq$  25°C. If Ta > 25°C, derate by 1.2 mW/°C.
- 5. Ta  $\leq$  25°C. If Ta > 25°C, derate by 4.0 mW/°C.
- 6. Ta  $\leq$  25°C. If Ta > 25°C, derate by 6.4 mW/°C.
- 7. 50 mm  $\times$  50 mm  $\times$  1.5mmt glass epoxy board(5% wiring density), Ta  $\leq$  25°C. If Ta > 25°C, derate by 5 mW/°C.
- 8. 15 mm  $\times$  25 mm  $\times$  0.7mmt alumina ceramic board,Ta  $\leq$  25°C. If Ta > 25°C, derate by 6.4 mW/°C.

### **Electrical Characteristics**

#### HA17431VLP/VP/VPJ/VUP/VLTP, HA17432VUP/VLTP

### $(Ta = 25^{\circ}C, I_{K} = 10 \text{ mA})$

Item	Symbol	Min	Тур	Max	Unit	Test Conditions	Notes
Reference voltage	Vref	2.475	2.500	2.525	V	$V_{KA} = Vref$	
Reference voltage temperature deviation	Vref(dev)	_	10	_	mV	$V_{KA} = Vref,$ Ta = -20°C to +85°C	1
Reference voltage temperature coefficient	∆Vref/∆Ta	_	±30	_	ppm/°C	V <sub>KA</sub> = Vref, 0°C to 50°C gradient	
Reference voltage regulation	$\Delta Vref/\Delta V_{\rm KA}$	_	2.0	3.7	mV/V	$V_{KA} = Vref to 16 V$	
Reference input current	Iref	_	2	6	μA	$R_1 = 10 \text{ k}\Omega, R_2 = \infty$	
Reference current temperature deviation	Iref(dev)	—	0.5	—	μΑ	$R_1 = 10 \text{ k}\Omega, R_2 = \infty,$ Ta = -20°C to +85°C	
Minimum cathode current	Imin	_	0.4	1.0	mA	$V_{KA} = Vref$	2
Off state cathode current	loff	_	0.001	1.0	μA	$V_{KA} = 16 V$ , $Vref = 0 V$	
Dynamic impedance	Z <sub>ka</sub>	_	0.2	0.5	Ω	$V_{_{KA}} = Vref,$ $I_{_{K}} = 1 mA to 50 mA$	
Bypass resistance	R <sub>PS</sub>	1.6	2.0	2.4	kΩ	I <sub>PS</sub> = 1 mA	3
Bypass resistance temperature coefficient	$\Delta R_{PS} / \Delta Ta$	_	+2000	_	ppm/°C	$I_{_{PS}} = 1 \text{ mA},$ 0°C to 50°C gradient	3

#### **Electrical Characteristics** (cont.)

#### HA17431PJ/PAJ/FPJ/FPAJ/P/A/UA/UPA/FP/FPA/PNA/PNAJ, HA17432UA/UPA

#### $(Ta = 25^{\circ}C, I_{K} = 10 \text{ mA})$

Item	Symbol	Min	Тур	Max	Unit	Test Cond	itions	Notes
Reference voltage	Vref	2.440	2.495	2.550	V	$V_{KA} = Vref$		А
		2.395	2.495	2.595	-			Normal
Reference voltage temperature deviation	Vref(dev)	_	11	(30)	mV	$V_{KA} = Vref$	Ta = -20°C to +85°C	1, 4
		_	5	(17)	_		Ta = 0°C to +70°C	1, 4
Reference voltage	$\Delta \text{Vref} / \Delta \text{V}_{\text{\tiny KA}}$	_	1.4	3.7	mV/V	V <sub>KA</sub> = Vref t	o 10 V	
regulation		_	1	2.2	_	V <sub>KA</sub> = 10 V	to 40 V	
Reference input current	Iref	_	3.8	6	μA	$R_1 = 10 \text{ k}\Omega$	, $R_2 = \infty$	
Reference current temperature deviation	Iref(dev)	_	0.5	(2.5)	μA	$R_1 = 10 k\Omega$ Ta = 0°C to	, R₂ = ∞, o +70°C	4
Minimum cathode current	Imin		0.4	1.0	mA	$V_{KA} = Vref$		2
Off state cathode current	loff	_	0.001	1.0	μA	$V_{_{KA}} = 40 V,$	Vref = 0 V	
Dynamic impedance	Z <sub>KA</sub>	_	0.2	0.5	Ω	$V_{\kappa A} = Vref,$ $I_{\kappa} = 1 mA to$	o 100 mA	
Notes: 1. Vref(dev	) = Vref(max)	– Vref(mii	n)					

Vref(dev) Ta Min Ta Max

2. Imin is given by the cathode current at Vref =  $Vref_{(IK=10mA)} - 15 \text{ mV}$ .

3.  $R_{_{PS}}$  is only provided in HA17431VLP.

4. The maximum value is a design value (not measured).



### MPAK-5(5-pin), MPAK(3-pin) and UPAK Marking Patterns

The marking patterns shown below are used on MPAK-5, MPAK and UPAK products. Note that the product code and mark pattern are different. The pattern is laser-printed.



Notes: 1. Boxes (1) to (5) in the figures show the position of the letters or numerals, and are not actually marked on the package.

Product	(1)	(2)	
HA17431VLP	4	Р	
HA17431VUP	4	R	
HA17432VUP	4	S	
HA17431VLTP	3	A	
HA17432VLTP	3	В	
HA17431UA	4	A	
HA17431UPA	4	В	
HA17432UA	4	С	
HA17432UPA	4	F	

2. The letters (1) and (2) show the product specific mark pattern.

3. The letter (3) shows the production year code (the last digit of the year) for UPAK products.

4. The bars (a), (b) and (c) show a production year code for MPAK-5 and MPAK products as shown below. After 2010 the code is repeated every 8 years.

Year	2002	2003	2004	2005	2006	2007	2008	2009
(a)	None	None	None	Bar	Bar	Bar	Bar	None
(b)	None	Bar	Bar	None	None	Bar	Bar	None
(c)	Bar	None	Bar	None	Bar	None	Bar	None

5. The letter (4) shows the production month code (see table below).

Production month	Jan.	Feb.	Mar.	Apr.	May.	Jun.	Jul.	Aug.	Sep.	Oct.	Nov.	Dec.
Marked code	А	В	С	D	Е	F	G	Н	J	К	L	М

6. The letter (5) shows manufacturing code. For UPAK products.



### **Characteristics Curves**

#### HA17431VLP/VP/VPJ/VUP/VLTP, HA17432VUP/VLTP





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#### HA17431PJ/PAJ/FPJ/FPAJ/P/PA/UA/UPA/FP/FPA/PNA/PNAJ, HA17432UA/UPA







### **Application Examples**

As shown in the figure on the right, this IC operates as an inverting amplifier, with the REF pin as input pin. The open-loop voltage gain is given by the reciprocal of "reference voltage deviation by cathode voltage change" in the electrical specifications, and is approximately 50 to 60 dB. The REF pin has a high input impedance, with an input current Iref of 3.8  $\mu$ A Typ (V version: Iref = 2  $\mu$ A Typ). The output impedance of the output pin K (cathode) is defined as dynamic impedance  $Z_{KA}$ , and  $Z_{KA}$  is low (0.2  $\Omega$ ) over a wide cathode current range. A (anode) is used at the minimum potential, such as ground.



Figure 1 Operation Diagram

### **Application Hints**

No.	Application Example	Description
1	Reference voltage generation circuit Vin O	This is the simplest reference voltage circuit. The value of the resistance R is set so that cathode current $I_{\kappa} \ge 1$ mA.
		Output is fixed at Vout $\cong$ 2.5 V.
		The external capacitor $C_{L}$ ( $C_{L} \ge 3.3 \ \mu F$ ) is used to prevent oscillation in normal applications.
2	Variable output shunt regulator circuit	This is circuit 1 above with variable output provided.
	$Vin \bigcirc \bigvee \bigvee \qquad \bullet \qquad \bullet \qquad \bullet \qquad \bigcirc Vout$ $R \qquad \qquad Iref \qquad K$ $R_1 \ge   K$	Here, Vout $\cong$ 2.5 V $\times \frac{(R_1 + R_2)}{R_2}$
		Since the reference input current Iref = $3.8 \mu A$ Typ (V version: Iref = $2 \mu A$ Typ) flows through R <sub>1</sub> , resistance values are chosen to allow the resultant voltage drop to be imported
		be ignored.

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#### Application Hints (cont.)



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#### Application Hints (cont.)



#### Design Guide for AC-DC SMPS (Switching Mode Power Supply)

#### Use of Shunt Regulator in Transformer Secondary Side Control

This example is applicable to both forward transformers and flyback transformers. A shunt regulator is used on the secondary side as an error amplifier, and feedback to the primary side is provided via a photocoupler.



Figure 2 Typical Shunt Regulator/Error Amplifier

#### Determination of External Constants for the Shunt Regulator

**DC characteristic determination:** In figure 2,  $R_1$  and  $R_2$  are protection resistor for the light emitting diode in the photocoupler, and  $R_2$  is a bypass resistor to feed  $I_k$  minimum, and these are determined as shown below. The photocoupler specification should be obtained separately from the manufacturer. Using the parameters in figure 2, the following formulas are obtained:

$$R_1 = \frac{V_0 - V_F - V_K}{I_F + I_B}$$
,  $R_2 = \frac{V_F}{I_B}$ 

 $V_{\kappa}$  is the HA17431 operating voltage, and is set at around 3 V, taking into account a margin for fluctuation.  $R_2$  is the current shunt resistance for the light emitting diode, in which a bias current  $I_{B}$  of around 1/5  $I_{F}$  flows.

Next, the output voltage can be determined by R3 and R4, and the following formula is obtained:

$$V_0 = \frac{R_3 + R_4}{R_4} \times Vref, Vref = 2.5 V Typ$$

The absolute values of  $R_3$  and  $R_4$  are determined by the HA17431 reference input current Iref and the AC characteristics described in the next section. The Iref value is around 3.8  $\mu$ A Typ. (V version: 2  $\mu$ A Typ)

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**AC characteristic determination:** This refers to the determination of the gain frequency characteristic of the shunt regulator as an error amplifier. Taking the configuration in figure 2, the error amplifier characteristic is as shown in figure 3.





In Figure 3, the following formulas are obtained:

Gain

 $G_{_1}$  =  $G_{_0} \approx 50~dB$  to 60 dB (determined by shunt regulator)

$$G_2 = \frac{R_5}{R_3}$$

Corner frequencies

 $f_1 = 1/(2\pi C_1 G_0 R_3)$  $f_2 = 1/(2\pi C_1 R_5)$ 

 $G_0$  is the shunt regulator open-loop gain; this is given by the reciprocal of the reference voltage fluctuation  $\Delta V ref / \Delta V_{KA}$ , and is approximately 50 dB.

#### **Practical Example**

Consider the example of a photocoupler, with an internal light emitting diode  $V_F = 1.05$  V and  $I_F = 2.5$  mA, power supply output voltage  $V_2 = 5$  V, and bias resistance  $R_2$  current of approximately 1/5  $I_F$  at 0.5 mA. If the shunt regulator  $V_K = 3$  V, the following values are found.

$$R_{1} = \frac{5V - 1.05V - 3V}{2.5mA + 0.5mA} = 316(\Omega) (330\Omega \text{ from E24 series})$$
$$R_{2} = \frac{1.05V}{0.5mA} = 2.1(k\Omega) (2.2k\Omega \text{ from E24 series})$$

Next, assume that  $R_3 = R_4 = 10 \text{ k}\Omega$ . This gives a 5 V output. If  $R_5 = 3.3 \text{ k}\Omega$  and  $C_1 = 0.022 \mu\text{F}$ , the following values are found.

$$\begin{split} G_{_2} &= 3.3 \text{ k}\Omega \ / \ 10 \text{ k}\Omega = 0.33 \text{ times} \ (-10 \text{ dB}) \\ f_{_1} &= 1 \ / \ (2 \times \pi \times 0.022 \ \mu\text{F} \times 316 \times 10 \ \text{k}\Omega) = 2.3 \ (\text{Hz}) \\ f_{_2} &= 1 \ / \ (2 \times \pi \times 0.022 \ \mu\text{F} \times 3.3 \ \text{k}\Omega) = 2.2 \ (\text{kHz}) \end{split}$$

### **Package Dimensions**















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